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#### PS20341-N



#### INTEGRATED POWER FUNCTIONS

500V/3A low-loss 4th generation (planar) IGBT inverter bridge for 3 phase DC-to-AC power conversion.

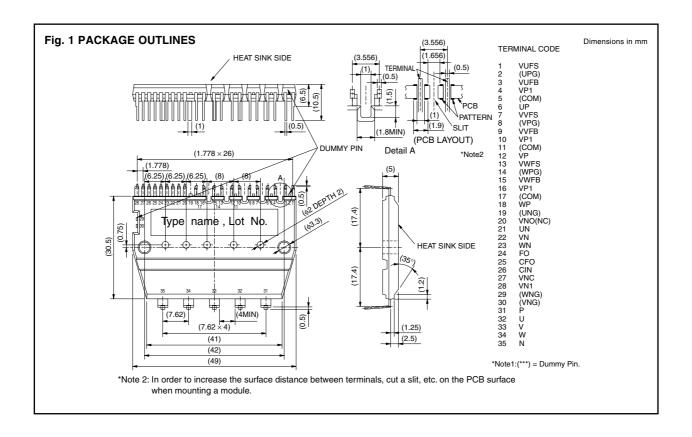
#### INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For upper-leg IGBTs: Drive circuit, High voltage isolated high-speed level shifting, Control circuit under-voltage (UV) protection.

  Note: Bootstrap supply scheme can be applied.
- For lower-leg IGBTs: Drive circuit, Control circuit under-voltage protection (UV), Short-circuit protection (SC).
- Fault signaling: Corresponding to a SC fault (Low-side IGBT) or a UV fault (Low-side IGBT).
- Input interface: 5V line CMOS/TTL compatible, Schmitt Trigger receiver circuit.

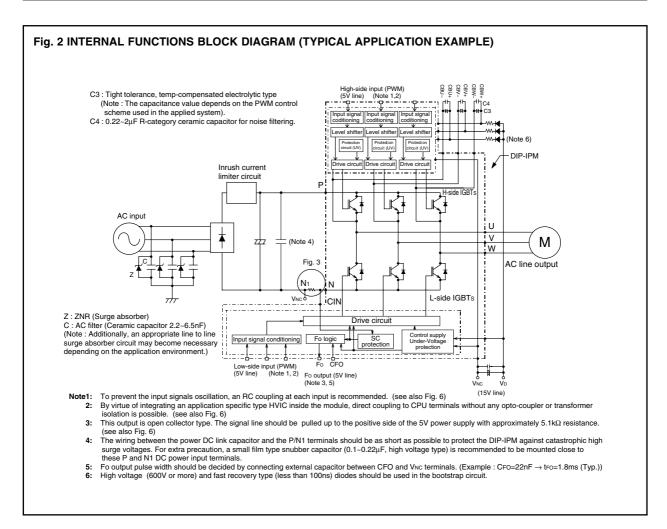
# **APPLICATION**

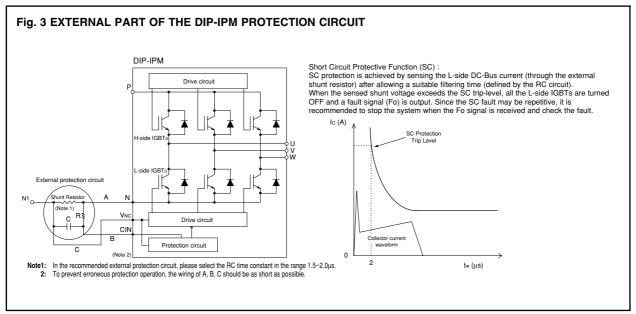
AC100V~200V inverter drive for motor control.





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# **MAXIMUM RATINGS** ( $T_j = 25^{\circ}C$ , unless otherwise noted)

#### **INVERTER PART**

Symbol	Parameter	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	350	V
VCC(surge)	Supply voltage (surge)	Applied between P-N	400	V
VCES	Collector-emitter voltage		500	V
±lc	Each IGBT collector current	Tf = 25°C	3	Α
±ICP	Each IGBT collector current (peak)	Tf = 25°C, instantaneous value (pulse)	6	Α
Pc	Collector dissipation	Tf = 25°C, per 1 chip	17.8	W
Tj	Junction temperature	(Note 1)	-20~+150	°C

Note 1 : The maximum junction temperature rating of the power chips integrated within the DIP-IPM is  $150^{\circ}$ C (@ Tf  $\leq$   $100^{\circ}$ C). However, to ensure safe operation of the DIP-IPM, the average junction temperature should be limited to Tj(ave)  $\leq$   $125^{\circ}$ C (@ Tf  $\leq$   $100^{\circ}$ C).

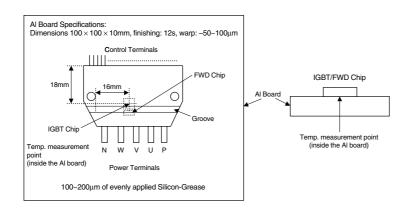
#### **CONTROL (PROTECTION) PART**

Symbol	Parameter	Condition	Ratings	Unit
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC	20	V
VDB	Control supply voltage	Applied between Vufb-Vufs, Vvfb-Vvfs, Vwfb-Vwfs	20	٧
VCIN	Input voltage	Applied between UP, VP, WP-VNC, UN, VN, WN-VNC	-0.5~VD+0.5	٧
VFO	Fault output supply voltage	Applied between Fo-VNC	-0.5~VD+0.5	V
IFO	Fault output current	Sink current at Fo terminal	15	mA
Vsc	Current sensing input voltage	Applied between CIN-VNC	-0.5~VD+0.5	V

### **TOTAL SYSTEM**

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Self protection supply voltage limit (short-circuit protection capability)	VD = VDB = 13.5~16.5V, Inverter part Tj = 125°C, non-repetitive, less than 2 $\mu$ s	330	V
Tf	Heat-fin operation temperature	(Note 2)	-20~+100	°C
Tstg	Storage temperature		<b>−</b> 40~+125	°C
Viso	Isolation voltage	60Hz, Sinusoidal, 1 minute, connection pins to heat-sink plate	1500	Vrms

#### Note 2: Tf MEASUREMENT POINT





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#### THERMAL RESISTANCE

Cumphial	Davamatav	Condition		Limits			1.1-24
Symbol Parameter		Condition		Min.	Тур.	Max.	Unit
Rth(j-f)Q	Junction-to-heat sink thermal	Inverter IGBT part (per 1/6 module) (N	lote 3)	_	_	7.0	°C/W
Rth(j-f)F	resistance	Inverter FWD part (per 1/6 module) (N	lote 3)	_		8.0	°C/W

Note 3 : Grease with good thermal conductivity should be applied evenly about +100μm~+200μm on the contact surface of a DIP-IPM and a heat sink.

#### **ELECTRICAL CHARACTERISTICS** (Tj = 25°C, unless otherwise noted)

#### INVERTER PART

0	Davis visate v	Condition		Limits			Limit		
Symbol	Parameter			Min.	Тур.	Max.	Unit		
VCE(sat)	Collector-emitter saturation	VD = VDB = 15V	Ic = 3A, Tj = 25°C	_	1.4	1.9	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
	voltage	VCIN = 0V	Ic = 3A, Tj = 125°C	_	1.5	2.05	٧		
VEC	FWD forward voltage	$T_j = 25^{\circ}C$ , $-IC = 3A$ , $VCIN = 5V$		_	1.9	2.6	V		
ton		15V	0.4	0.9	1.35	μs			
trr	Switching times IC = 3A, T <sub>j</sub> = 125°C Inductive load (upper-lower a			_	0.25	_	μs		
tc(on)			ver arm)	_	0.35	0.60	μs		
toff		$VCIN = 5 \leftrightarrow 0V$	,	_	1.10	1.55	μs		
tc(off)						_	0.65	1.40	μs
ICES	Collector-emitter cut-off	VCE = VCES	Tj = 25°C	_	_	1	mA		
	current	VCE = VCES	Tj = 125°C	_	_	10	IIIA		

#### **CONTROL (PROTECTION) PART**

0	Danamatan	Parameter Condition		Limits			Unit
Symbol	Parameter		Condition	Min.	Тур.	Max.	Unit
		VD = VDB =15V	Total of VP1-VNC, VN1-VNC	_	_	8.5	mΛ
ID	Circuit current	VCIN = 5V	VUFB-VUFS, VVFB-VVFS, VWFB-VWFS	_	_	1.0	mA
טו	Circuit current	VD = VDB =15V	Total of VP1-VNC, VN1-VNC	_	_	9.7	mΛ
		VCIN = 0V	VUFB-VUFS, VVFB-VVFS, VWFB-VWFS	_	_	1.0	mA
VFOH		Vsc = 0V, Fo = 10	Vsc = 0V, Fo = $10k\Omega$ 5V pull-up		_	_	V
VFOL	Fault output voltage	VSC = 1V, IFO = 1.	.5mA	_	0.6	0.9	V
VFOsat	1	VSC = 1V, IFO = 1	5mA	0.8	1.2	1.8	V
VSC(ref)	Short-circuit trip level	Tj = 25°C, VD = 15	5V (Note 4)	0.43	0.48	0.53	V
UVDBt			Trip level	10.0	_	12.0	V
UVDBr	Supply circuit under-voltage	T <sub>i</sub> ≤ 125°C	Reset level	10.5	_	12.5	V
UVDt	protection	1] ≤ 125 C	Trip level	10.3	_	12.5	V
UVDr			Reset level	10.8	_	13.0	V
tFO	Fault output pulse width	CFO = 22nF (Note 5)		1.0	1.8	_	ms
Vth(on)	ON threshold voltage	Applied between:		0.8	1.4	2.0	V
Vth(off)	OFF threshold voltage	UP, VP, WP-VNC, I	Un, Vn, Wn-Vnc	2.5	3.0	4.0	V

Note 4: Short-circuit protection operates only at the low-arms. Please select the value of the external shunt resistor such that the SC trip level is less than 5.1A



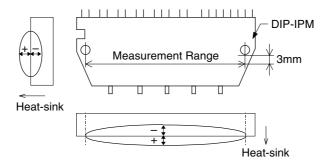
<sup>5:</sup> Fault signal is outputted when the low-arm short-circuit or control supply under-voltage protective functions operate. The fault output pulse-width tFo depends on the capacitance value of CFO according to the following approximate equation. : CFO = (12.2 × 10<sup>-6</sup>) × tFO [F]

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# **MECHANICAL CHARACTERISTICS AND RATINGS**

Parameter	Condition		Limits			Limit
Parameter	Condition		Min.	Тур.	Max.	Unit
Mounting torque	Mounting screw : M3	_	0.59	0.78	0.98	N⋅m
Terminal pulling strength	Weight 9.8N	EIAJ-ED-4701	10	_	_	S
Bending strength	Weight 4.9N. 90deg bend	EIAJ-ED-4701	2	_	_	times
Weight		_	_	20	_	g
Heat-sink flatness	(Note 6	) —	-50	_	100	μm

# Note 6: Measurement point of heat-sink flatness



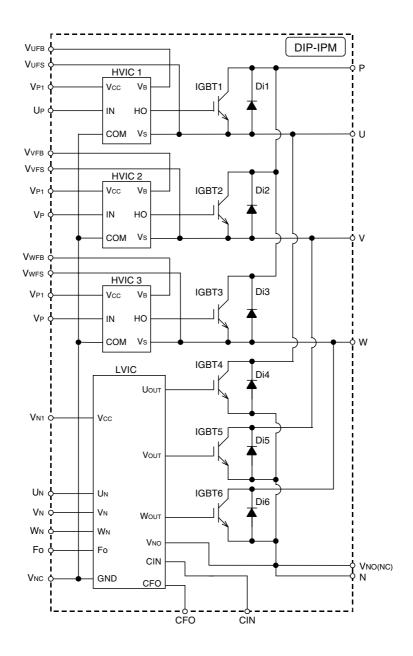
# RECOMMENDED OPERATION CONDITIONS

Cumbal	Parameter Condition	O constitutions		Limits		
Symbol	Parameter	Parameter Condition		Тур.	Max.	Unit
Vcc	Supply voltage	Applied between P-N		280	330	V
VD	Control supply voltage	Applied between VP1-VNC, VN1-VNC	13.5	15.0	16.5	V
VDB	Control supply voltage	Applied between Vufb-Vufs, Vvfb-Vvfs, Vwfb-Vwfs	13.5	15.0	16.5	V
$\Delta V$ D, $\Delta V$ DB	Control supply variation		-1	_	1	V/μs
tdead	Arm shoot-through blocking time	For each input signal	1.5	_	_	μs
fPWM	PWM input frequency	T <sub>j</sub> ≤ 125°C, T <sub>f</sub> ≤ 100°C	_	5	_	kHz
VCIN(ON)	Input ON voltage	Applied between LID VID VID VID LIV VID VID	0~0.65			V
VCIN(OFF)	Input OFF voltage	Applied between UP, VP, WP-VNC, UN, VN, WN-VNC		4.0~5.5		



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Fig. 4 THE DIP-IPM INTERNAL CIRCUIT



Note: The IGBTs gates and the HVICs COM terminals are connected to the dummy pins.



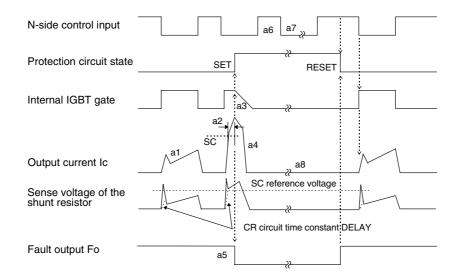
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#### Fig. 5 TIMING CHARTS OF THE DIP-IPM PROTECTIVE FUNCTIONS

#### [A] Short-Circuit Protection (N-side only)

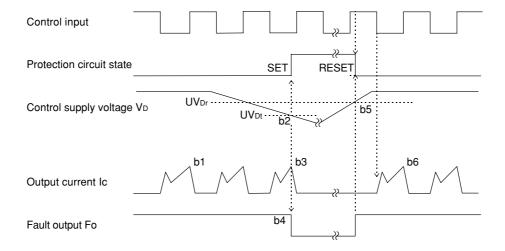
(For the external shunt resistor and CR connection, please refer to Fig. 3.)

- a1. Normal operation: IGBT ON and carrying current.
- a2. Short-circuit current detection (SC trigger).
- a3. IGBT gate interrupt.
- a4. IGBT turns OFF.
- a5. Fo timer operation starts: The pulse width of the Fo signal is set by the external capacitor CFo.
- a6. Input "H": IGBT OFF state. a7. Input "L": IGBT ON state.
- a8. IGBT OFF state.



#### [B] Under-Voltage Protection (N-side, UVD)

- b1. Normal operation: IGBT ON and carrying current.
- b2. Under-voltage trip (UVDt).b3. IGBT OFF in spite of control input condition.
- b4. Fo timer operation starts.
- b5. Under-voltage reset (UVDr)
- b6. Normal operation: IGBT ON and carrying current.





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### [C] Under-Voltage Protection (P-side, UVDB)

- c1. Control supply voltage rises: After the voltage level reachs UVDBr, the circuits start to operate when the next input is applied. c2. Normal operation: IGBT ON and carrying current. c3. Under-voltage trip (UVDBt).

- c4. IGBT OFF in spite of control input condition (there is no Fo signal output).
- c5. Under-voltage reset (UVDBr).
- c6. Normal operation: IGBT ON and carrying current.

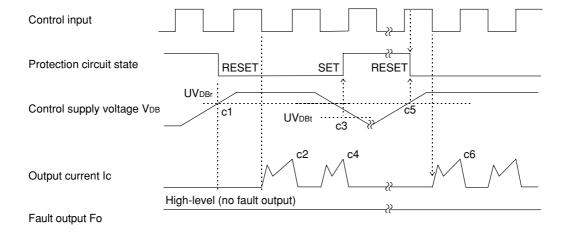
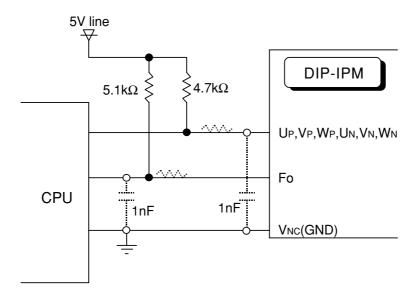


Fig. 6 RECOMMENDED CPU I/O INTERFACE CIRCUIT



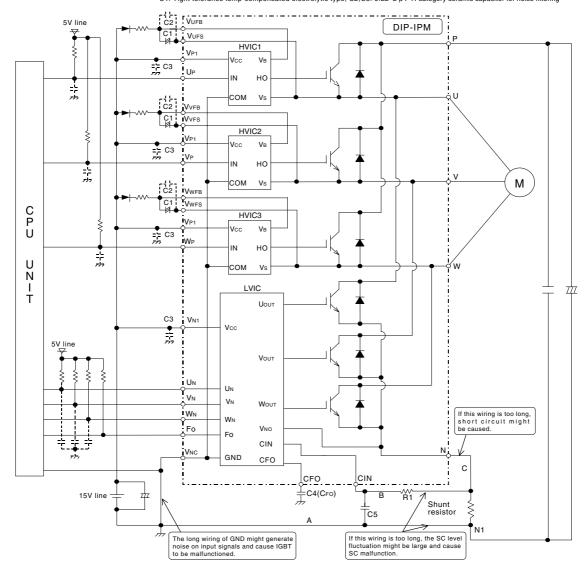
Note: RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and on the wiring impedance of the application's printed circuit board.



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Fig. 7 TYPICAL DIP-IPM APPLICATION CIRCUIT EXAMPLE

C1: Tight tolerance temp\*compensated electrolytic type; C2,C3: 0.22-2  $\mu$  F R\*category ceramic capacitor for noise filtering



Note 1: To prevent the input signals oscillation, an RC coupling at each input is recommended, and the wiring of each input should be as short as possible (less than 2cm).

- 2: By virtue of integrating an application specific type HVIC inside the module, direct coupling to CPU terminals without any opto-coupler or transformer isolation is possible
- 3: Fo output is open collector type. This signal line should be pulled up to the positive side of the 5V power supply with approximately 5.1k $\Omega$  resistance.
- 4: FO output pulse width should be decided by connecting an external capacitor between CFO and VNC terminals (CFO). (Example: CFO = 22 nF  $\rightarrow$  tFO = 1.8 ms (typ.))
- 5: Each input signal line should be pulled up to the positive side of the 5V power supply with approximately 4.7kΩ resistance (other RC coupling circuits at each input may be needed depending on the PWM control scheme used and on the wiring impedances of the system's printed circuit board). Approximately a 0.22-2µF by-pass capacitor should be used across each power supply connection terminals.
- 6: To prevent errors of the protection function, the wiring of A, B, C should be as short as possible.
  7: In the recommended protection circuit, please select the R1Cs time constant in the range of 1.5~2μs.
- 8: Each capacitor should be put as nearby the terminals of the DIP-IPM as possible.
- 9: To prevent surge destruction, the wiring between the smoothing capacitor and the P&N1 terminals should be as short as possible. Approximately a 0.1~0.22μF snubber capacitor between the P&N1 terminals is recommended.

